

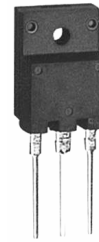


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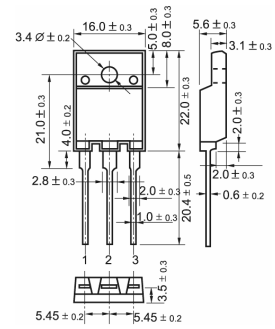
SILICON DIFFUSED POWER TRANSISTOR

GENERAL DESCRIPTION

Highvoltage,high-speed switching npn transistors in a plastic envelope with integrated efficiency diode , primarily for use in horizontal deflection circuites of colour television receivers



TO-3PML



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|-------------|---------------------------------------|--|-----|------|---------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0V$ | | 1500 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | | 600 | V |
| I_C | Collector current (DC) | | | 6 | A |
| I_{CM} | Collector current peak value | | | 12 | A |
| P_{tot} | Total power dissipation | $T_{mb} \leq 25^\circ C$ | | 60 | W |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 5.0A; I_B = 1.0A$ | | 5 | V |
| I_{csat} | Collector saturation current | $f = 16KHz$ | | | A |
| V_F | Diode forward voltage | $I_F = 5.0A$ | | 1.5 | V |
| t_f | Fall time | $I_C = 4A, I_{B1} = -1/2 I_{B2} = 0.8A, V_{CC} = 100V$ | | 1.0 | μs |

LIMITING VALUES

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|------------|---------------------------------------|--------------------------|-----|------|------------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0V$ | | 1500 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | | 600 | V |
| V_{EBO} | Emitter-base voltage(open collector) | | | 5 | V |
| I_C | Collector current (DC) | | | 6 | A |
| I_B | Base current (DC) | | | 2 | A |
| I_{BM} | Base current peak value | | | 4 | A |
| P_{tot} | Total power dissipation | $T_{mb} \leq 25^\circ C$ | | 60 | W |
| T_{sto} | Storage temperature | | -55 | 150 | $^\circ C$ |
| T_j | Junction temperature | | | 150 | $^\circ C$ |

ELECTRICAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|---------------|---|--|-----|-----|---------|
| I_{CE} | Collector-emitter cut-off current | $V_{BE} = 0V; V_{CE} = V_{CESMmax}$ | | 1.0 | mA |
| I_{CES} | | $V_{BE} = 0V; V_{CE} = V_{CESMmax}$ | | 2.0 | mA |
| $V_{CEOsust}$ | Collector-emitter sustaining voltage | $T_j = 125^\circ C$ $I_B = 0A; I_C = 100mA$ $L = 25mH$ | | | V |
| V_{CEsat} | Collector-emitter saturation voltages | $I_C = 5.0A; I_B = 1.0A$ | | 5.0 | V |
| V_{BESat} | Base-emitter saturation voltage | $I_C = 5.0A; I_B = 1.0A$ | | 1.5 | V |
| h_{FE} | DC current gain | $I_C = 1.0A; V_{CE} = 5V$ | 8 | 30 | |
| V_F | Diode forward voltage | $I_F = 5.0A$ | | 1.5 | V |
| f_T | Transition frequency at $f = 1MHz$ | $I_C = 0.1A; V_{CE} = 10V$ | 3 | | MHz |
| C_c | Collector capacitance at $f = 1MHz$ | $V_{CB} = 10V$ | | | pF |
| t_s | Switching times(16KHz line deflecton circuit) | $I_C = 4A, I_{B1} = -1/2 I_{B2} = 0.8A, V_{CC} = 100V$ | | | μs |
| t_f | Turn-off storage time Turn-off fall time | $I_C = 4A, I_{B1} = -1/2 I_{B2} = 0.8A, V_{CC} = 100V$ | | 1.0 | μs |